



# PSMN012-60YS

N-channel LFPAK 60 V, 11.1 m $\Omega$  standard level MOSFET

Rev. 01 — 5 January 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference

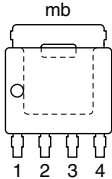
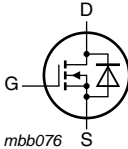
| Symbol                         | Parameter                                    | Conditions  | Min | Typ  | Max | Unit |
|--------------------------------|--|---|-----|------|-----|------|
| V <sub>DS</sub>                | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   | -   | -    | 60  | V    |
| I <sub>D</sub>                 | drain current                                | T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V;<br>see <a href="#">Figure 1</a>  | -   | -    | 59  | A    |
| P <sub>tot</sub>               | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>   | -   | -    | 89  | W    |
| T <sub>j</sub>                 | junction temperature                         |   | -55 | -    | 175 | °C   |
| <b>Avalanche ruggedness</b>    |  |   |     |      |     |      |
| E <sub>DS(AL)S</sub>           | non-repetitive drain-source avalanche energy | V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C;<br>I <sub>D</sub> = 59 A; V <sub>sup</sub> ≤ 60 V;<br>R <sub>GS</sub> = 50 $\Omega$ | -   | -    | 71  | mJ   |
| <b>Dynamic characteristics</b> |  |   |     |      |     |      |
| Q <sub>GD</sub>                | gate-drain charge                            | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 30 A;  | -   | 6.4  | -   | nC   |
| Q <sub>G(tot)</sub>            | total gate charge                            | V <sub>DS</sub> = 30 V; see <a href="#">Figure 14</a> and <a href="#">15</a>  | -   | 28.4 | -   | nC   |

Table 1. Quick reference ...continued

| Symbol                        | Parameter                           | Conditions   | Min | Typ | Max  | Unit |
|-------------------------------|-------------------------------------|--|-----|-----|------|------|
| <b>Static characteristics</b> |                                     |  |     |     |      |      |
| $R_{DS(on)}$                  | drain-source<br>on-state resistance | $V_{GS} = 10\text{ V}; I_D = 15\text{ A};$<br>$T_j = 100\text{ °C};$ see <a href="#">Figure 12</a> | -   | -   | 17.8 | mΩ   |
|                               |                                     | $V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C};$<br>see <a href="#">Figure 13</a>    | -   | 8   | 11.1 | mΩ   |

## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------------------------|--|---|
| 1   | S      | source                            |  |  |
| 2   | S      | source                            |  |   |
| 3   | S      | source                            |  |   |
| 4   | G      | gate                              |  |   |
| mb  | D      | mounting base; connected to drain |  |   |

SOT669 (LPAK)

## 3. Ordering information

Table 3. Ordering information

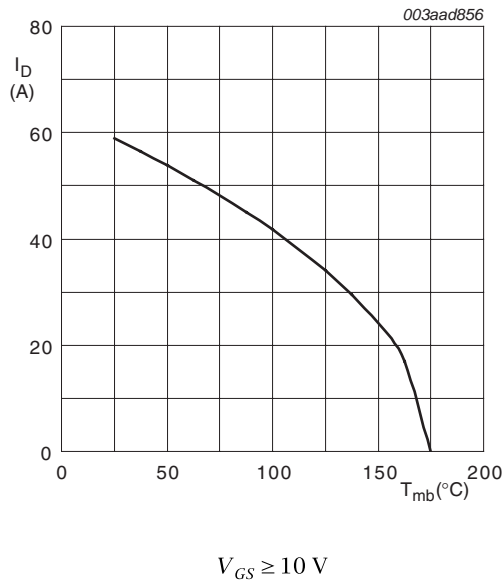
| Type number  | Package |  | Version |
|--------------|---------|--|---------|
|              | Name    | Description  |         |
| PSMN012-60YS | LPAK    | plastic single-ended surface-mounted package (LPAK); 4 leads | SOT669  |

## 4. Limiting values

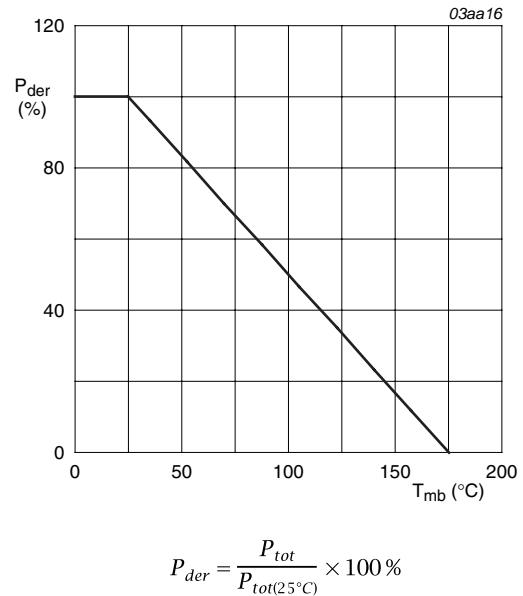
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

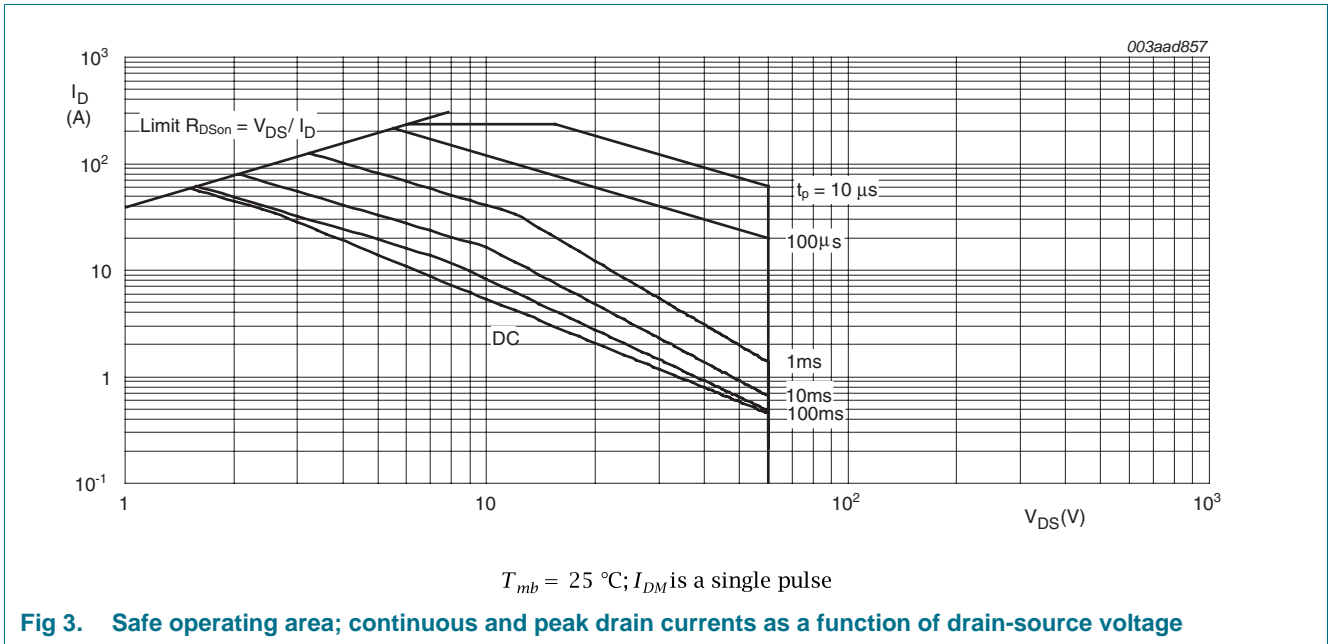
| Symbol                      | Parameter                                    | Conditions  | Min | Max | Unit |
|-----------------------------|--|---|-----|-----|------|
| $V_{DS}$                    | drain-source voltage                         | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$   | -   | 60  | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$   | -   | 60  | V    |
| $V_{GS}$                    | gate-source voltage                          |   | -20 | 20  | V    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>   | -   | 42  | A    |
|                             |  | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>  | -   | 59  | A    |
| $I_{DM}$                    | peak drain current                           | $t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>                                 | -   | 236 | A    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>  | -   | 89  | W    |
| $T_{stg}$                   | storage temperature                          |   | -55 | 175 | °C   |
| $T_j$                       | junction temperature                         |   | -55 | 175 | °C   |
| $T_{sld(M)}$                | peak soldering temperature                   |   | -   | 260 | °C   |
| <b>Source-drain diode</b>   |  |   |     |     |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$   | -   | 59  | A    |
| $I_{SM}$                    | peak source current                          | $t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$  | -   | 236 | A    |
| <b>Avalanche ruggedness</b> |  |   |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 59\text{ A}; V_{sup} \leq 60\text{ V}; R_{GS} = 50\text{ }\Omega$ | -   | 71  | mJ   |



**Fig 1. Continuous drain current as a function of mounting base temperature**



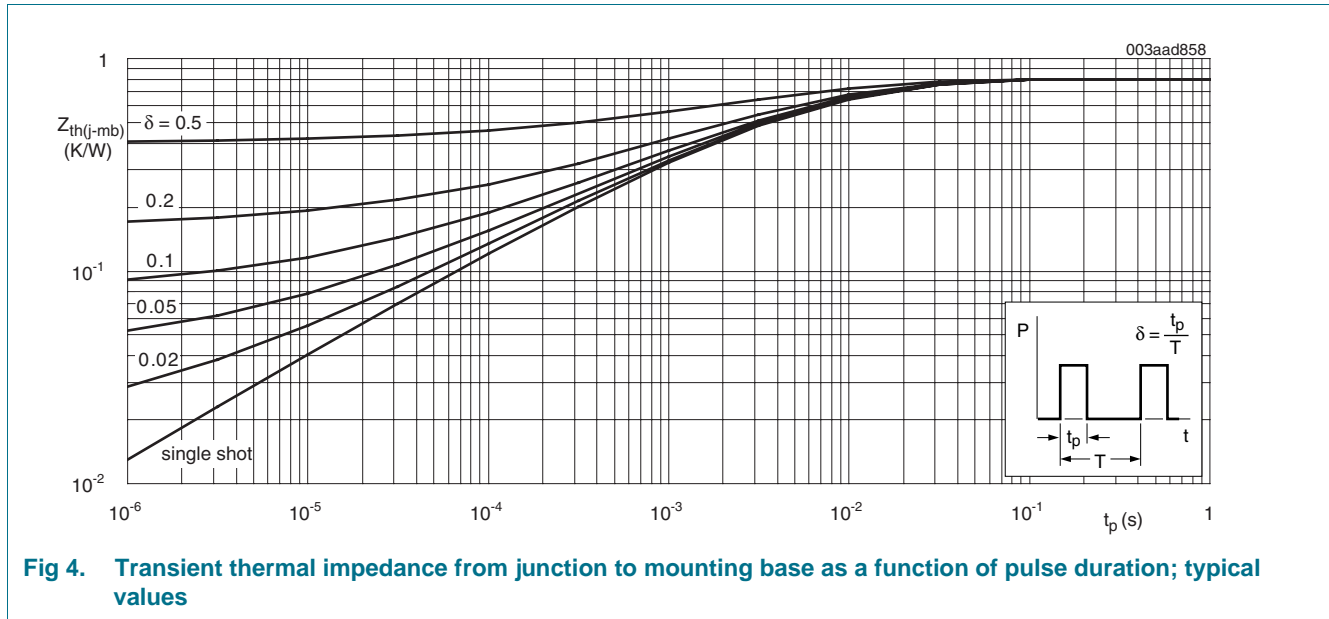
**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



## 5. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol         | Parameter   | Conditions                   | Min | Typ | Max  | Unit |
|----------------|---|------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <a href="#">Figure 4</a> | -   | 0.8 | 1.68 | K/W  |



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values**

## 6. Characteristics

**Table 6. Characteristics**

| Symbol                         | Parameter                         | Conditions  | Min  | Typ  | Max  | Unit          |
|--------------------------------|-----------------------------------|---|------|------|------|---------------|
| <b>Static characteristics</b>  |                                   |   |      |      |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage    | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$   | 54   | -    | -    | V             |
|                                |                                   | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | 60   | -    | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage     | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 10</a> and <a href="#">11</a>     | 2    | 3    | 4    | V             |
| $V_{GSth}$                     |                                   | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a>                           | -    | -    | 4.6  | V             |
|                                |                                   | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a>                           | 0.95 | -    | -    | V             |
| $I_{DSS}$                      | drain leakage current             | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -    | 0.03 | 2    | $\mu\text{A}$ |
|                                |                                   | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$   | -    | -    | 50   | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current              | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -    | 2    | 100  | nA            |
|                                |                                   | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$   | -    | 2    | 100  | nA            |
| $R_{DSon}$                     | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>                     | -    | 17   | 25.5 | mΩ            |
|                                |                                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a>                     | -    | -    | 17.8 | mΩ            |
|                                |                                   | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 13</a>                      | -    | 8    | 11.1 | mΩ            |
| $R_G$                          | gate resistance                   | $f = 1 \text{ MHz}$   | -    | 0.66 | -    | Ω             |
| <b>Dynamic characteristics</b> |                                   |   |      |      |      |               |
| $Q_{G(tot)}$                   | total gate charge                 | $I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>         | -    | 28.4 | -    | nC            |
|                                |                                   | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$  | -    | 23.3 | -    | nC            |
| $Q_{GS}$                       | gate-source charge                | $I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>         | -    | 8.75 | -    | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge  | $I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a>                                | -    | 4.9  | -    | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge |   | -    | 3.9  | -    | nC            |
| $Q_{GD}$                       | gate-drain charge                 | $I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>         | -    | 6.4  | -    | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage       | $V_{DS} = 30 \text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>  | -    | 4.8  | -    | V             |
| $C_{iss}$                      | input capacitance                 | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 16</a> | -    | 1685 | -    | pF            |
| $C_{oss}$                      | output capacitance                |   | -    | 245  | -    | pF            |
| $C_{riss}$                     | reverse transfer capacitance      |   | -    | 140  | -    | pF            |
| $t_{d(on)}$                    | turn-on delay time                | $V_{DS} = 30 \text{ V}; R_L = 1 \text{ } \Omega; V_{GS} = 10 \text{ V}$ ;<br>$R_{G(ext)} = 4.7 \text{ } \Omega$                   | -    | 15.2 | -    | ns            |
| $t_r$                          | rise time                         |   | -    | 12.6 | -    | ns            |
| $t_{d(off)}$                   | turn-off delay time               |   | -    | 28.7 | -    | ns            |
| $t_f$                          | fall time                         |   | -    | 8.2  | -    | ns            |

Table 6. Characteristics ...continued

| Symbol                    | Parameter             | Conditions   | Min | Typ  | Max | Unit |
|---------------------------|-----------------------|--|-----|------|-----|------|
| <b>Source-drain diode</b> |                       |  |     |      |     |      |
| $V_{SD}$                  | source-drain voltage  | $I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a> | -   | 0.82 | 1.2 | V    |
| $t_{rr}$                  | reverse recovery time | $I_S = 10\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;              | -   | 35   | -   | ns   |
| $Q_r$                     | recovered charge      | $V_{DS} = 30\text{ V}$   | -   | 41   | -   | nC   |

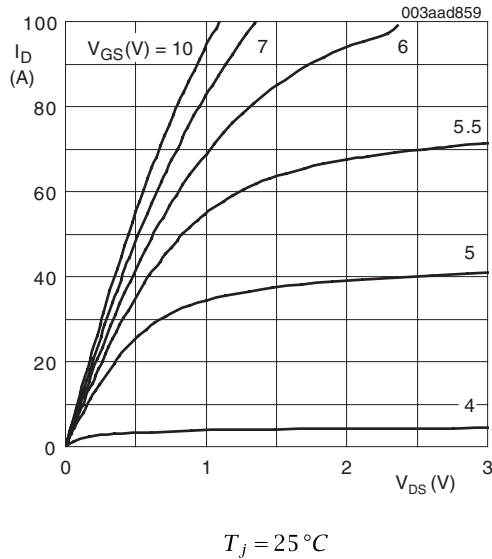


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

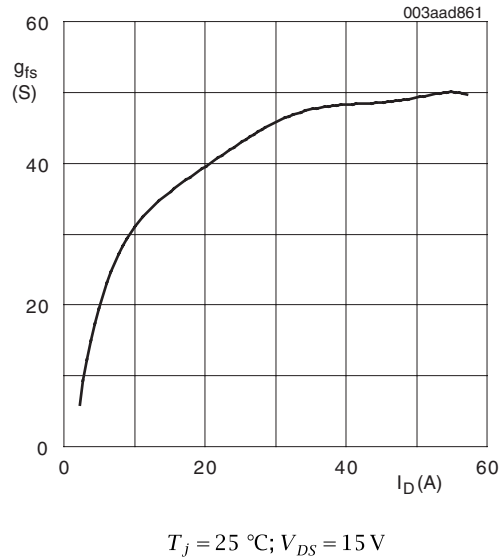


Fig 6. Forward transconductance as a function of drain current; typical values

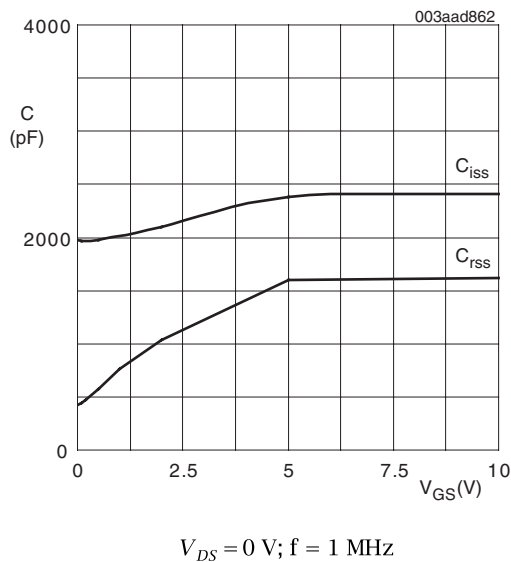


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

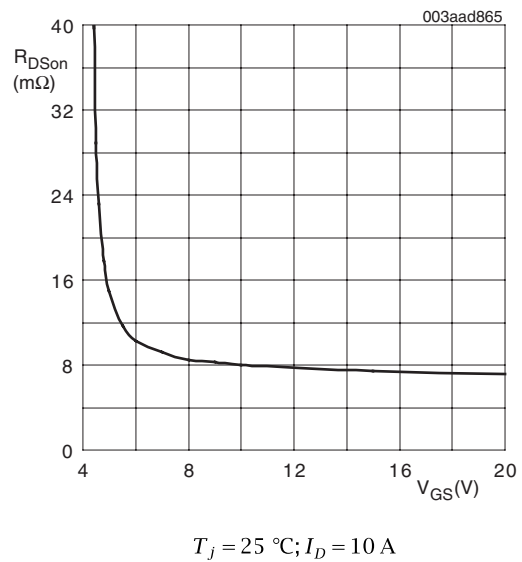
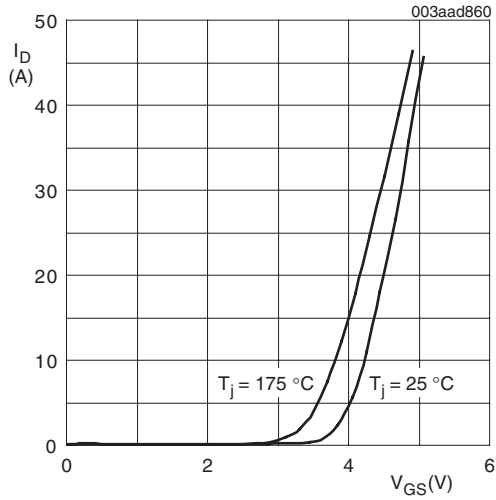
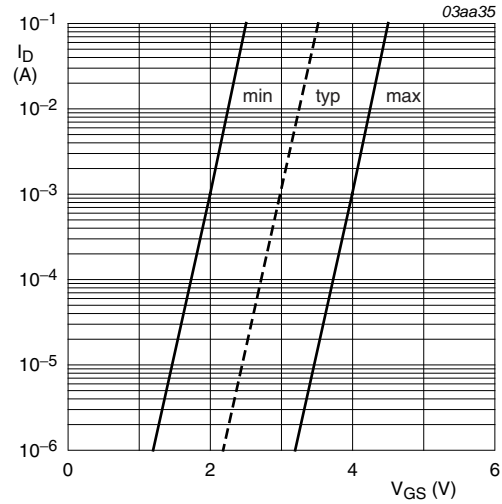


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



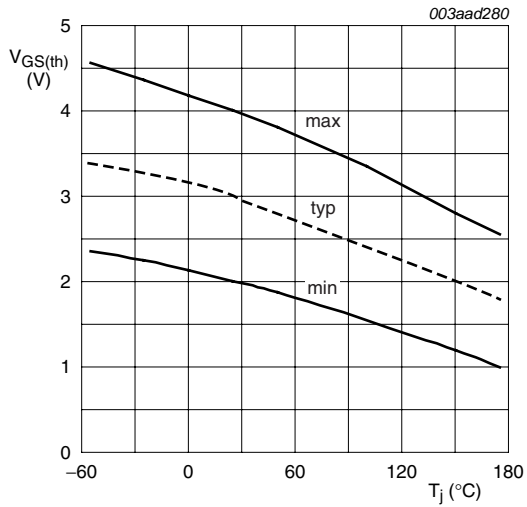
$$V_{DS} > I_D \times R_{DSon}$$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



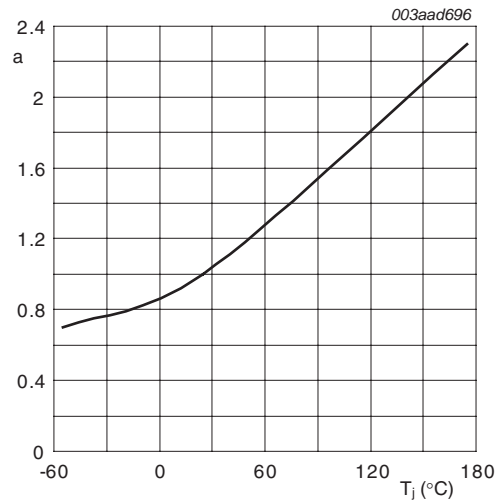
$$T_j = 25\text{ °C}; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

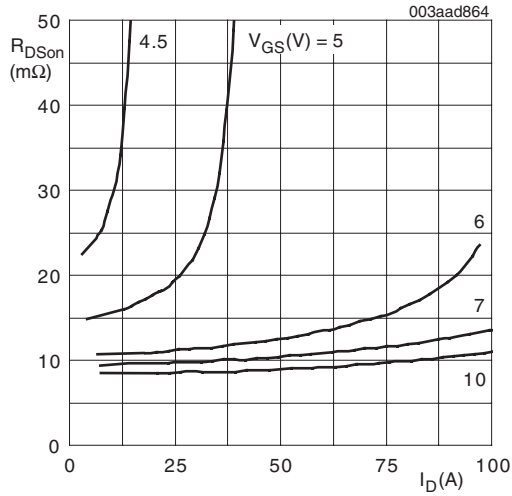
Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25\text{ °C})}}$$

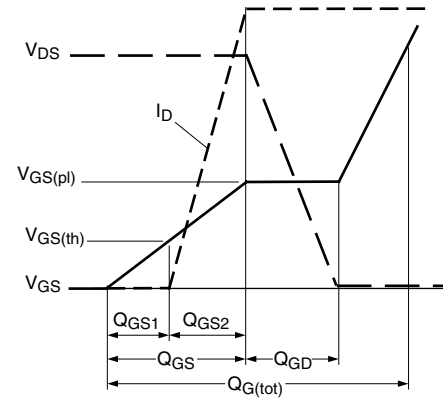
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.



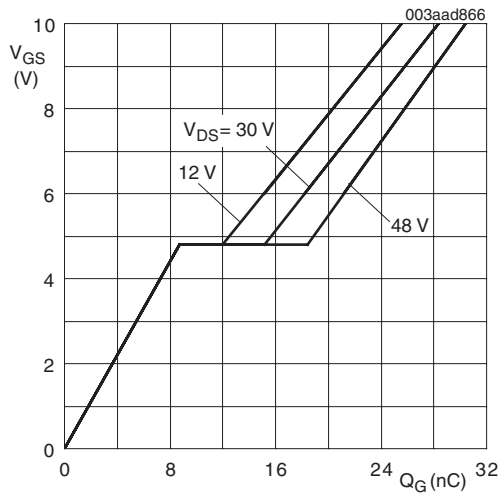


$T_j = 25^\circ C$

**Fig 13. Drain-source on-state resistance as a function of drain current; typical values**

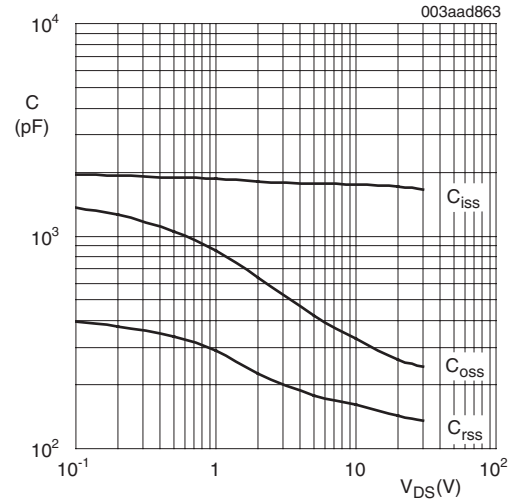


**Fig 14. Gate charge waveform definitions**



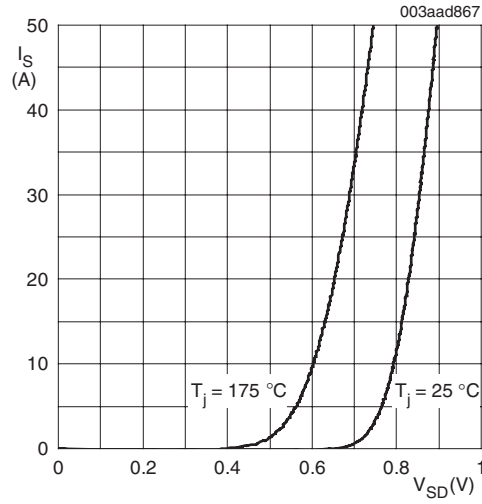
$T_j = 25^\circ C; I_D = 30$  A

**Fig 15. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0$  V;  $f = 1$  MHz

**Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0V$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

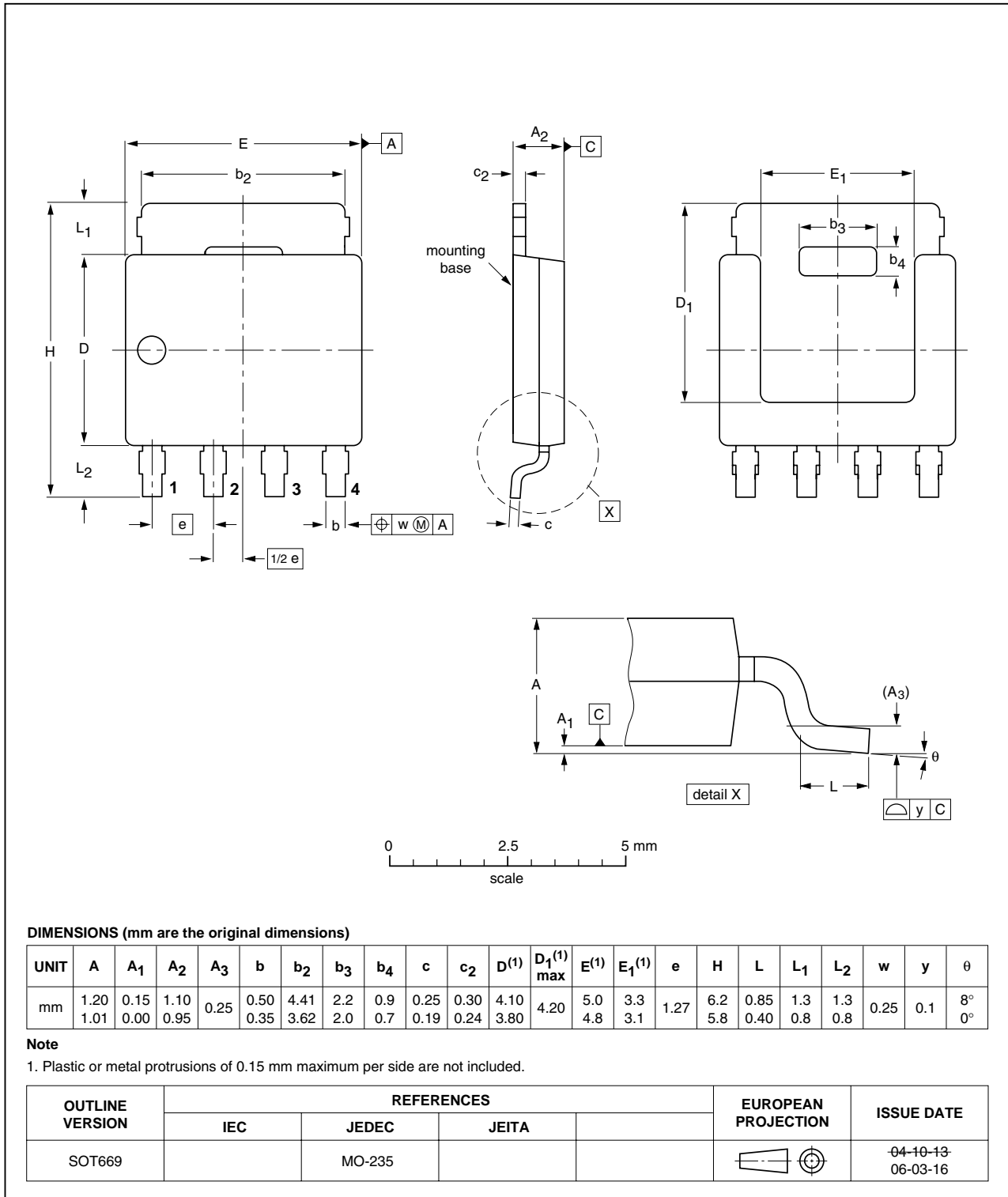


Fig 18. Package outline SOT669 (LPAK)

## 8. Revision history

Table 7. Revision history

| Document ID    | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PSMN012-60YS_1 | 20100105     | Product data sheet | -             | -          |

## 9. Legal information

### 9.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 10. Contact information

For more information, please visit: <http://www.nexperia.com>

For sales office addresses, please send an email to: [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)

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